



)CP52/-16

PNP SURFACE MOUNT TRANSISTOR

Features

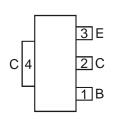
- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (DCP55)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

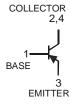
Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



SOT-223





TOP VIEW

Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current	I _{CM}	-1.5	A
Continuous Collector Current	Ic	-1	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Power Dissipation @ T _A = 25°C	р.	1 (Note 3)	W	
Power Dissipation @ 1A = 25 C	P_d	2 (Note 4)		
Operating and Storage Temperature Range	$T_{j,}T_{STG}$	-55 to +150	°C	
Thermal Resistance Junction to Ambient Air @ T _A = 25°C (Note 3)	$R_{\theta JA}$	125	°C/W	

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Conditions
OFF CHARACTERISTICS (Note 5)						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60	_		V	$I_C = -100 \mu A, I_E = 0A$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-60	_	_	V	$I_C = -10 \text{mA}, I_B = 0 \text{A}$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	_	_	V	$I_E = -10\mu A, I_C = 0A$
Collector Cut-Off Current		_	_	-100	nA	$V_{CB} = -30V, I_{E} = 0A$
	I _{CBO}	_		-20	μΑ	$V_{CB} = -30V$, $I_{E} = 0A$, $T_{A} = 150$ °C
Emitter Cut-Off Current	I _{EBO}	_	_	-10	μΑ	$V_{EB} = -5V, I_{C} = 0A$
ON CHARACTERISTICS (Note 5)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	_	-0.5	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	_	_	-1.0	V	$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
		40		250		$I_C = -150 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain	h _{FE}	25	_	_		$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
DCP52-16		100	_	250		$I_C = -150 \text{mA}, V_{CE} = -2 \text{V}$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f⊤		200		MHz	$I_C = -50 \text{mA}, V_{CE} = -5 \text{V},$ f = 100MHz

Note:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

 3. Device mounted on FR-4 PCB pad layout as shown on page 4 or on Diodes, Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 4. Device mounted on Polyimide PCB with a copper area of 1.8cm².
- 5. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%



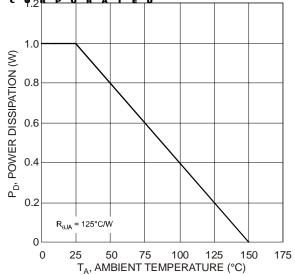


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

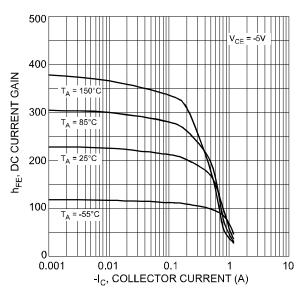


Fig. 3 Typical DC Current Gain vs. Collector Current

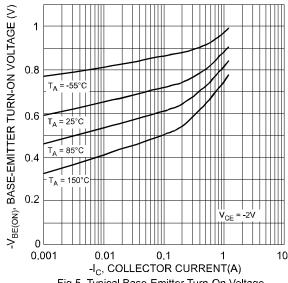


Fig 5. Typical Base-Emitter Turn-On Voltage vs. Collector Current

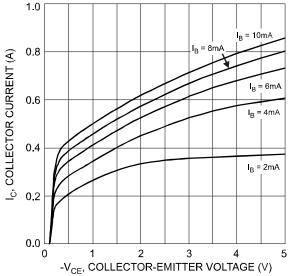


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

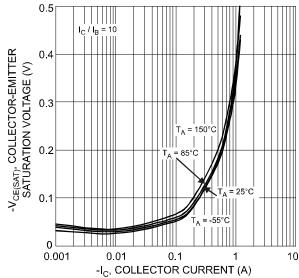


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

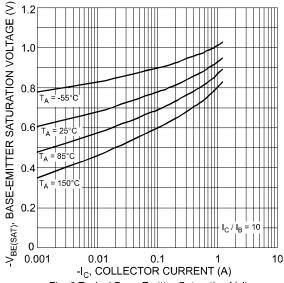
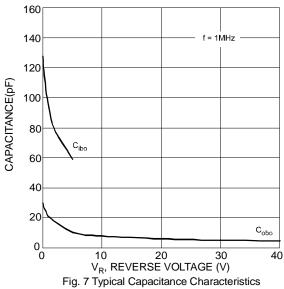


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current





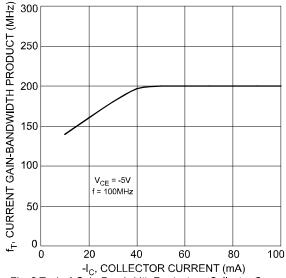


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

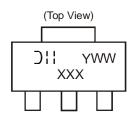
Ordering Information (Note 6)

Part Number	Case	Packaging
DCP52-13	SOT-223	2500 / Tape & Reel
DCP52-16-13	SOT-223	2500 / Tape & Reel

Note:

6. For packaging details, please visit our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

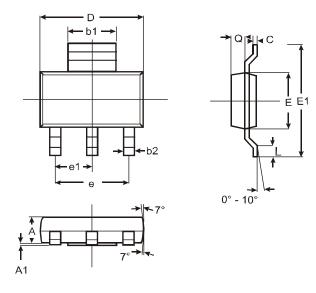


Oll = Manufacturer's code marking

XXX = Product type marking code Ex: P16 = DCP52 P16-16 = DCP52-16

YWW = Date code marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

Package Outline Dimensions

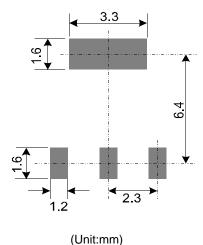


SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е			4.60		
e1	_	- 1	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

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Suggested Pad Layout: (Based on IPC-SM-782)



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